

# PerFE<sup>T</sup><sup>TM</sup> Power Transistor

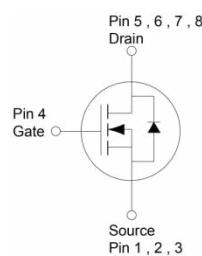
## FEATURES

- Ultra-low On-resistance
- 100% UIS and R<sub>g</sub> tested
- RoHS Compliant
- Halogen-Free according to IEC 61249-2-21

## APPLICATIONS

- DC-DC Converters
- Solenoid and Motor Drivers
- Load Switch

PRODUCT SUMMARY		
PARAMETER	VALUE	UNIT
V <sub>DS</sub>	40	V
R <sub>DS(on)</sub> (max)	V <sub>GS</sub> = 10V	5.6
	V <sub>GS</sub> = 4.5V	7.8
Q <sub>g</sub>	V <sub>GS</sub> = 4.5V	16
		nC



Note: MSL 1 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V <sub>DS</sub>	40	V
Gate-Source Voltage	V <sub>GS</sub>	±16	V
Continuous Drain Current, Silicon limited	I <sub>D</sub>	61	A
Continuous Drain Current	T <sub>C</sub> = 25°C	54	A
	T <sub>C</sub> = 100°C	38	
	T <sub>A</sub> = 25°C	16	
Pulsed Drain Current <sup>(Note 1)</sup>	I <sub>DM</sub>	216	A
Single Pulse Avalanche Current <sup>(Note 2)</sup>	I <sub>AS</sub>	20.7	A
Single Pulse Avalanche Energy <sup>(Note 2)</sup>	E <sub>AS</sub>	64.4	mJ
Total Power Dissipation	T <sub>C</sub> = 25°C	34	W
	T <sub>C</sub> = 125°C	6.8	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

THERMAL RESISTANCE			
PARAMETER	SYMBOL	MAXIMUM	UNIT
Thermal Resistance – Junction to Case	R <sub>θJC</sub>	3.7	°C/W
Thermal Resistance – Junction to Ambient	R <sub>θJA</sub>	53	°C/W

Note: R<sub>θJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins. R<sub>θJC</sub> is guaranteed by design while R<sub>θCA</sub> is determined by the user's board design.

<b>ELECTRICAL CHARACTERISTICS</b> ( $T_A = 25^\circ C$ unless otherwise noted)						
<b>PARAMETER</b>	<b>CONDITIONS</b>	<b>SYMBOL</b>	<b>MIN</b>	<b>TYP</b>	<b>MAX</b>	<b>UNIT</b>
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 1mA$	$BV_{DSS}$	40	--	--	V
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu A$	$V_{GS(TH)}$	1.4	1.8	2.2	V
Gate-Source Leakage Current	$V_{GS} = \pm 16V, V_{DS} = 0V$	$I_{GSS}$	--	--	$\pm 100$	nA
Drain-Source Leakage Current	$V_{GS} = 0V, V_{DS} = 40V$	$I_{DSS}$	--	--	1	$\mu A$
	$V_{GS} = 0V, V_{DS} = 40V$ $T_J = 125^\circ C$		--	--	100	
Drain-Source On-State Resistance (Note 3)	$V_{GS} = 10V, I_D = 27A$	$R_{DS(on)}$	--	4.3	5.6	$m\Omega$
	$V_{GS} = 4.5V, I_D = 27A$		--	5.5	7.8	
Forward Transconductance (Note 3)	$V_{DS} = 10V, I_D = 7A$	$g_{fs}$	--	57	--	S
<b>Dynamic</b>						
Total Gate Charge	$V_{GS} = 4.5V, V_{DS} = 20V,$ $I_D = 16A$	$Q_g$	--	16	--	nC
Total Gate Charge	$V_{GS} = 10V, V_{DS} = 20V,$ $I_D = 16A$	$Q_g$	--	33	--	
Gate-Source Charge		$Q_{gs}$	--	6.2	--	
Gate-Drain Charge		$Q_{gd}$	--	5.5	--	
Input Capacitance	$V_{GS} = 0V, V_{DS} = 25V,$ $f = 1.0MHz$	$C_{iss}$	--	2076	--	pF
Output Capacitance		$C_{oss}$	--	351	--	
Reverse Transfer Capacitance		$C_{rss}$	--	34	--	
Gate Resistance	$f = 1.0MHz$	$R_g$	--	1.8	--	$\Omega$
<b>Switching</b> (Note 4)						
Turn-On Delay Time	$V_{GS} = 10V, V_{DS} = 20V,$ $I_D = 16A, R_G = 1.8\Omega$	$t_{d(on)}$	--	8.9	--	ns
Rise Time		$t_r$	--	48	--	
Turn-Off Delay Time		$t_{d(off)}$	--	28	--	
Fall Time		$t_f$	--	7.1	--	
<b>Source-Drain Diode</b>						
Diode Forward Voltage (Note 3)	$V_{GS} = 0V, I_S = 27A$	$V_{SD}$	--	--	1.1	V
Reverse Recovery Time	$I_S = 16A,$ $di/dt = 100A/\mu s$	$t_{rr}$	--	34	--	ns
Reverse Recovery Charge		$Q_{rr}$	--	30	--	nC

**Notes:**

1. Package current limit.
2.  $L = 0.3mH, V_{GS} = 10V, R_G = 25\Omega$ , Starting  $T_J = 25^\circ C$ .
3. Pulse test: Pulse Width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
4. Switching time is essentially independent of operating temperature.

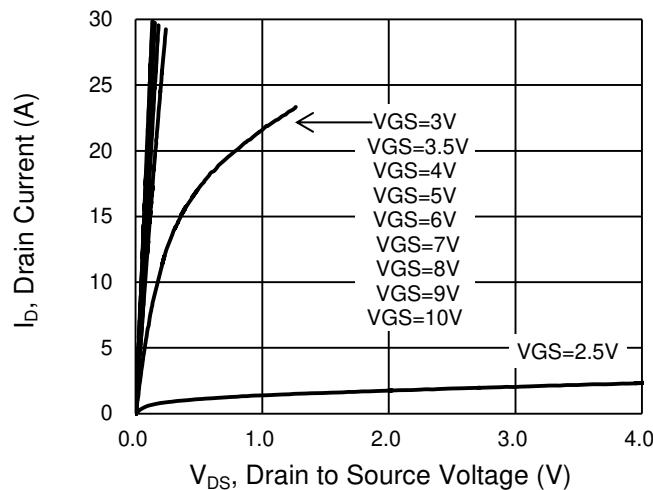
**ORDERING INFORMATION**

<b>ORDERING CODE</b>	<b>PACKAGE</b>	<b>PACKING</b>
TSM056NH04LCV RGG	PDFN33	5,000pcs / 13" Reel

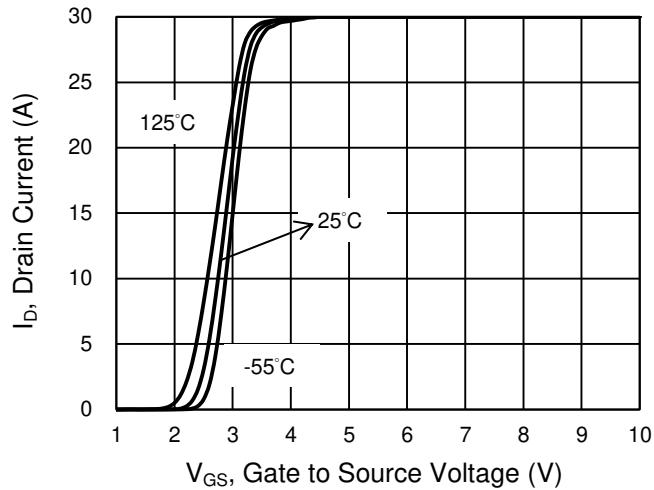
## CHARACTERISTICS CURVES

( $T_A = 25^\circ\text{C}$  unless otherwise noted)

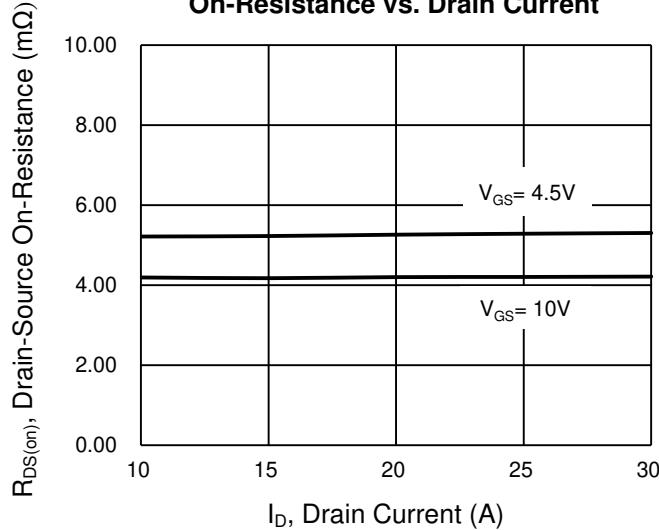
**Output Characteristics**



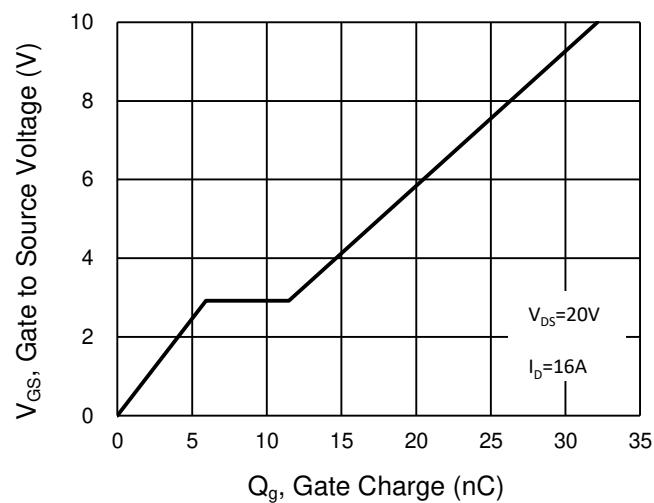
**Transfer Characteristics**



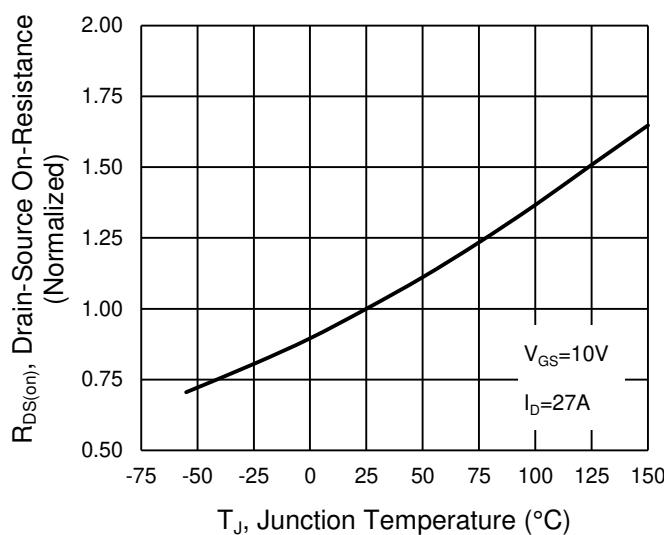
**On-Resistance vs. Drain Current**



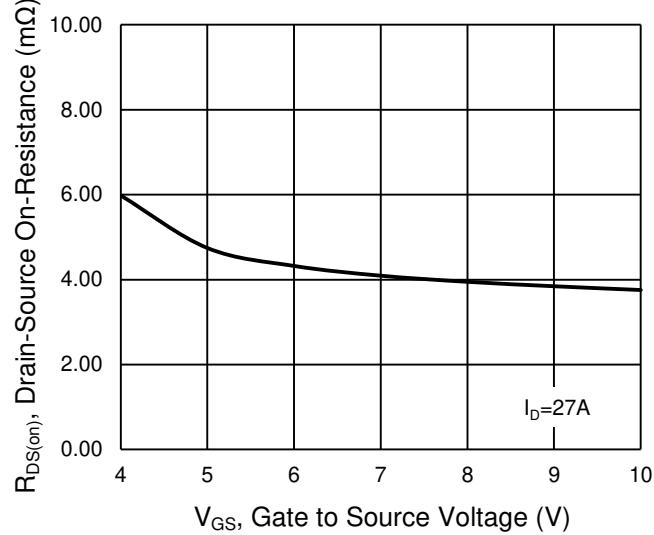
**Gate-Source Voltage vs. Gate Charge**



**On-Resistance vs. Junction Temperature**

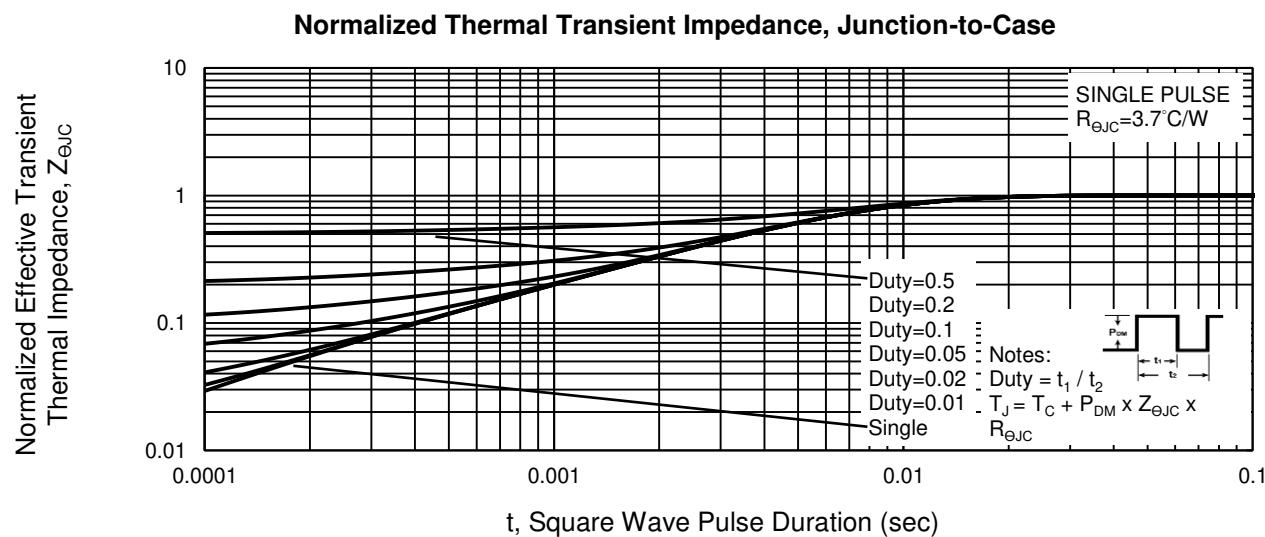
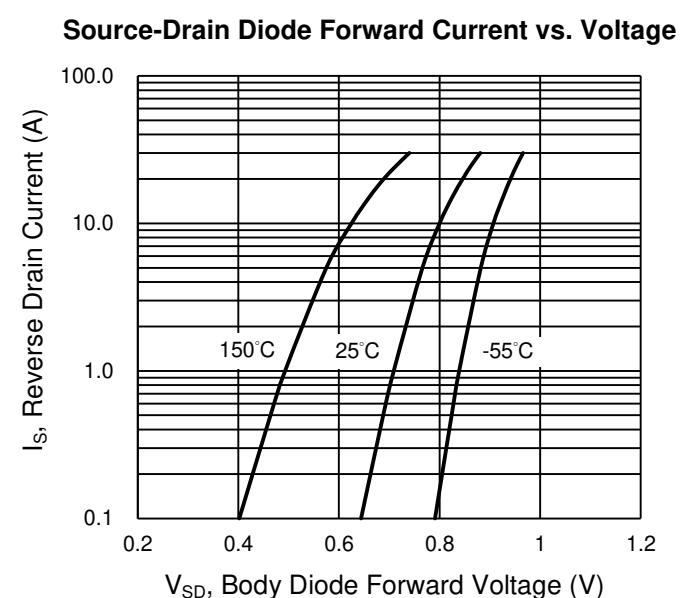
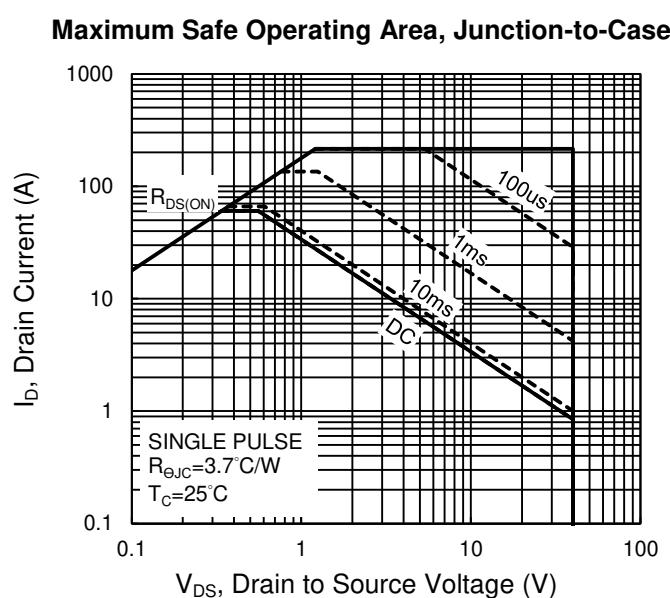
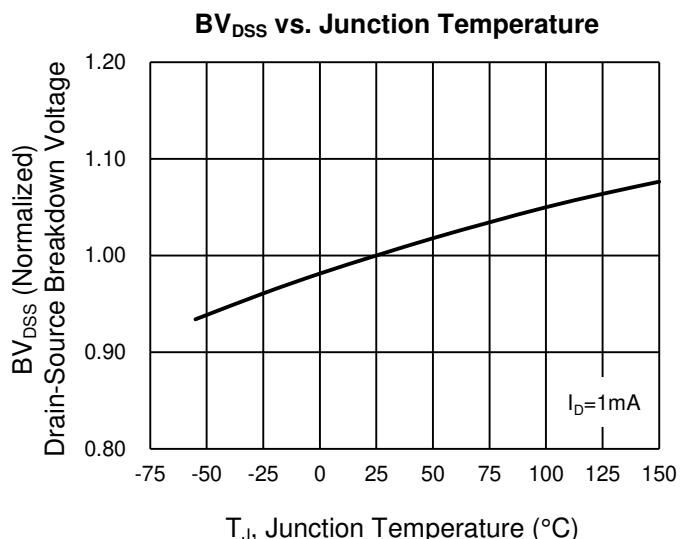
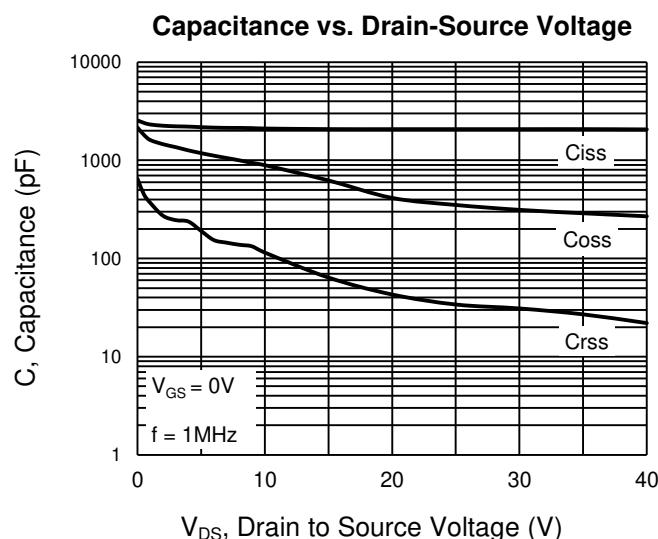


**On-Resistance vs. Gate-Source Voltage**



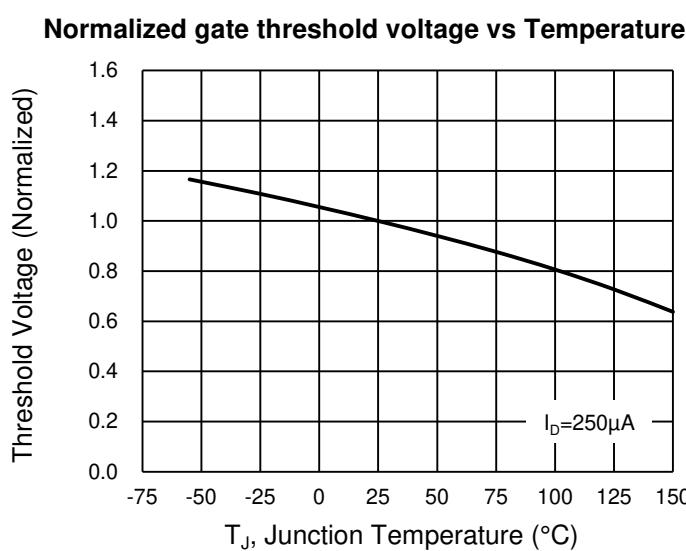
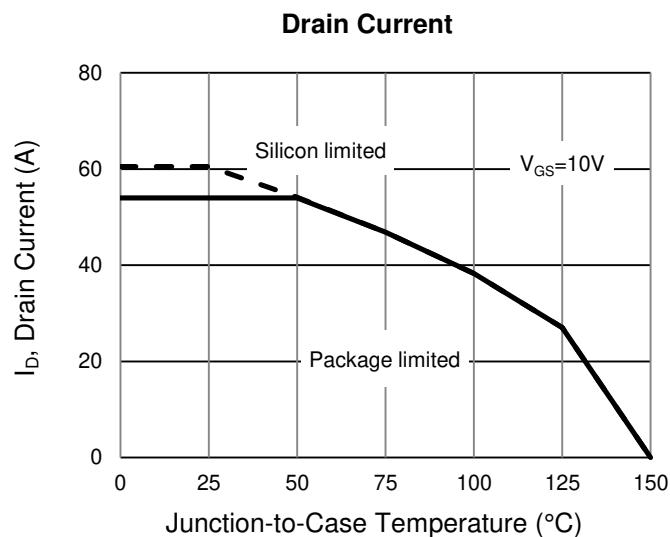
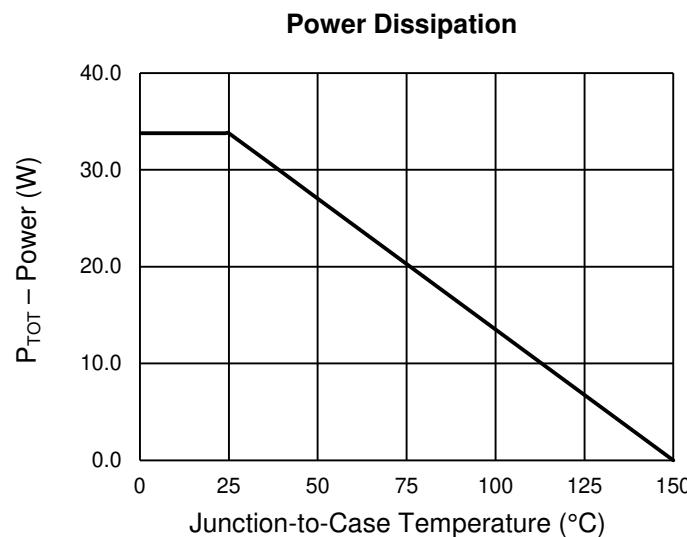
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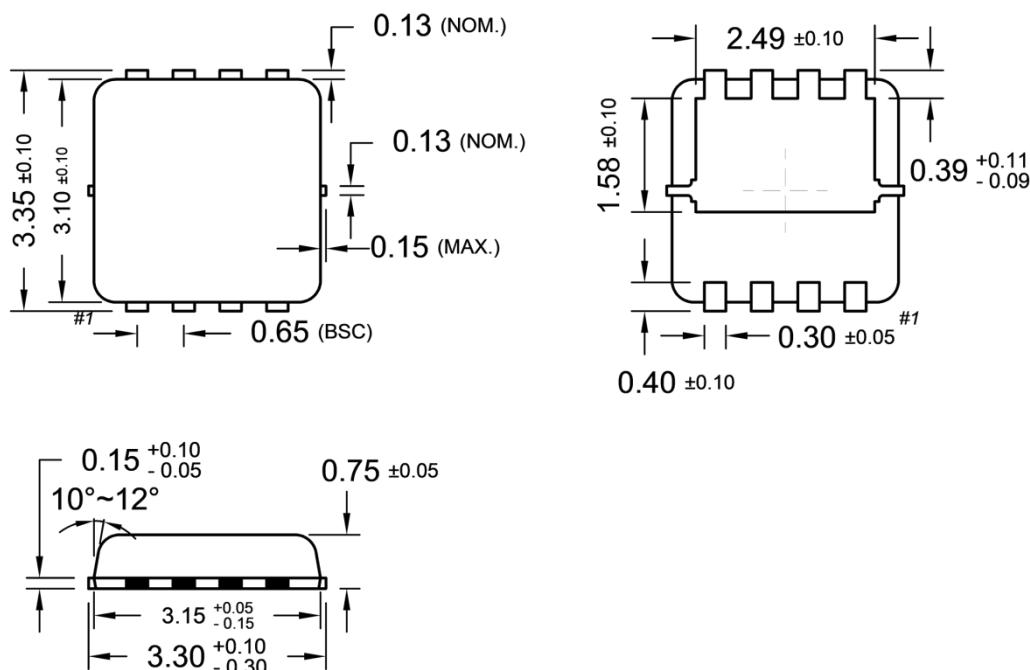
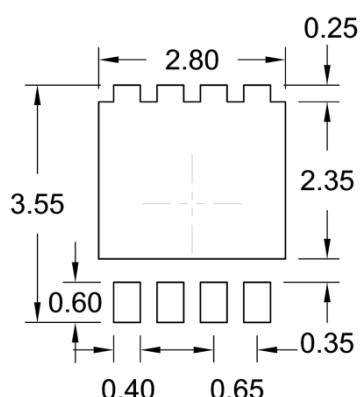


## CHARACTERISTICS CURVES

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**PACKAGE OUTLINE DIMENSIONS** (Unit: Millimeters)

**PDFN33**

**SUGGESTED PAD LAYOUT** (Unit: Millimeters)

**MARKING DIAGRAM**


- Y** = Year Code
- WW** = Week Code (01~52)
- L** = Lot Code (1~9,A~Z)
- F** = Factory Code

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